

General Description

The Sanrise SRC60R095BS is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC60R095BS break down voltage is 600V and it has a high rugged avalanche characteristics. The SRC60R095BS is available in TO-220F, TO-220C and TO-247 packages.

Features

- Ultra Low $R_{DS(ON)} = 95m\Omega @ V_{GS} = 10V$.
- Ultra Low Gate Charge, $Q_g = 120nC$ typ.
- Fast switching capability
- Robust design with better EAS performance
- EMI Improved
- Non-automotive Qualified
- Ultra-fast body diode

Application

- Telecom Power

Symbol

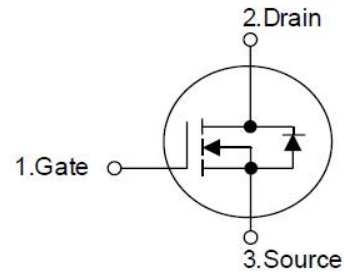


Figure 1 Symbol of SRC60R095BS

Package Type

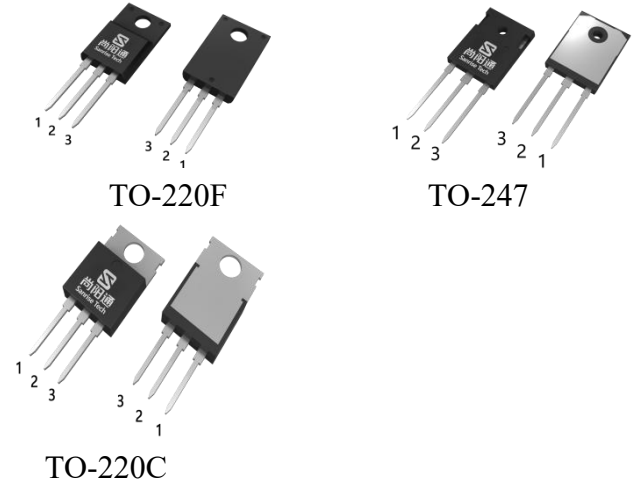


Figure 2 Package Types of SRC60R095BS

Ordering Information

SRC60R095BS□□-□		
Circuit Type	_____	E: Lead Free
Package	_____	G: Green
T: TO-247		Blank: Tube
TF: TO-220F		TR: Tape & Reel
TC: TO-220C		

Package	Part Number	Marking ID	Packing Type
TO-247	SRC60R095BST-G	SRC60R095BSTG	Tube
TO-220F	SRC60R095BSTF-G	SRC60R095BSTFG	Tube
TO-220C	SRC60R095BSTC-G	SRC60R095BSTCG	Tube

Absolute Maximum Ratings^{Note 1}

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage (static)		V_{GSS}	±20	V
Gate-Source Voltage (dynamic), AC ($f > 1$ Hz)		V_{GSS}	±30	V
Power Dissipation ($T_c = 25^\circ\text{C}$, TO-220F)		P_{tot}	32	W
Power Dissipation ($T_c = 25^\circ\text{C}$, TO-247, TO-220C)		P_{tot}	255	W
Continuous Drain Current	$T_c = 25^\circ\text{C}$	I_D	37	A
	$T_c = 100^\circ\text{C}$		23	
	$T_c = 125^\circ\text{C}$		16	
Pulsed Drain Current (Note 2)		I_{DM}	111	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	160	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	0.2	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	2.2	A
Continuous Diode Forward Current		I_S	37	A
Diode Pulse Current		$I_{S,PULSE}$	111	A
MOSFET dv/dt Ruggedness, $V_{DS} \leq 480\text{V}$		dv/dt	80	V/ns
Reverse Diode dv/dt , $V_{DS} \leq 480\text{V}$, $I_{SD} \leq I_D$		dv/dt	50	V/ns
Operating Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 to 150	$^\circ\text{C}$
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	$^\circ\text{C}$

Note:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $I_{AS} = 2.2\text{A}$, $V_{DD} = 60\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

Thermal characteristics

Parameter		Symbol	Min	Typ	Max	Unit
Thermal resistance, Junction-to-Case	TO-220F	R_{thJC}			3.9	$^\circ\text{C} / \text{W}$
	TO-247				0.49	
	TO-220C				0.49	
Thermal resistance, Junction-to-Ambient	TO-220F	R_{thJA}			78	$^\circ\text{C} / \text{W}$
	TO-247				60	
	TO-220C				60	

Electrical Characteristics

$T_J = 25^{\circ}\text{C}$, unless otherwise specified.

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250uA	600			V
Zero Gate Voltage Drain Current		I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	uA
Gate-Body Leakage Current	Forward	I _{GSSF}	V _{GS} =20V, V _{DS} =0V			100	nA
	Reverse	I _{GSSR}	V _{GS} =-20V, V _{DS} =0V			-100	
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} ,I _D =800uA	3.5	4.5	5.5	V
Static Drain-Source On-Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =20A		70	95	mΩ
Gate Resistance		R _G	f=1MHz, Open Drain		2.0		Ω
Dynamic Characteristics							
Input Capacitance		C _{ISS}	V _{DS} =400V, V _{GS} =0V, f=100kHz		2.4		nF
Output Capacitance		C _{OSS}			67		pF
Effective output capacitance, energy related ^{NOTE5}		C _{O(er)}	V _{GS} =0V, V _{DS} =0...480V		75		pF
Effective output capacitance, time related ^{NOTE6}		C _{O(tr)}			514		
Turn-on Delay Time		t _{d(on)}	V _{DD} =400V, I _D =20A R _G =3.3Ω, V _{GS} =10V		30		ns
Rise Time		t _r			7.3		
Turn-off Delay Time		t _{d(off)}			85		
Fall Time		t _f			5		
Gate Charge Characteristics							
Gate to Source Charge		Q _{gs}	V _{DD} =480V, I _D =20A V _{GS} =0 to 10V		29		nC
Gate to Drain Charge		Q _{gd}			62		
Gate Charge Total		Q _g			120		
Gate Plateau Voltage		V _{plateau}			6.7		V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V, I _{SD} =20A		0.86	1.1	V
Reverse Recovery Time		t _{rr}	V _R =400V, I _F =20A dI _F /dt=100A/us		150		ns
Reverse Recovery Charge		Q _{rr}			1.4		uC
Peak Reverse Recovery Current		I _{rrm}			17		A

Note:

- $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 480V
- $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 480 V



Shenzhen Sanrise Technology Co., LTD

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Main Site:

- Headquarter

Shenzhen Sanrise Technology Co., LTD.
A1206, Skyworth building, No. 008, gaoxinnan 1st Road,
Gaoxin District, Yuehai street,, Nanshan District, ShenZhen,
P.R.China
Tel: +86-755-22953335
Fax: +86-755-22916878

- Shanghai Office

Shenzhen Sanrise Technology Co., LTD
Rm.401, Building B, No. 666, Zhangheng Road,
Zhangjiang Hi-Tech Park, Shanghai, P.R.China
Tel: +86-21-68825918